

**SEMICONDUCTOR DEVICES HAVING CONTACT PLUGS AND LOCAL
INTERCONNECTS AND METHODS FOR MAKING THE SAME**

Abstract

5 Provided is, for example, a method for the fabrication of electrical interconnects in semiconductor devices wherein a substrate including two or more transistors having gate regions wherein the gate regions are not exposed (e.g., the gate regions are completely covered by an insulating cap) is provided. An insulating layer overlying the transistors and the active areas is deposited, where upon a hard mask is created
10 10 and patterned to form a contact plug/interconnect opening over a first active area and a portion of a first transistor immediately adjacent the first active area. A spacer is formed within the contact plug/interconnect opening. Insulating material overlying active areas between transistors is removed. A portion of the gate region of the first transistor is then exposed and interconnect material is deposited within the contact plug/interconnect opening
15 15 onto the exposed portion of the gate region of the first transistor and the first active area.